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EFC6605R

N-Channel Power MOSFET 20V, 10A, 13.3mΩ, Dual EFCP

Features

- 2.5V drive
- Protection diode in
- Halogen free compliance
- Common-drain type
- 2KV ESD HBM

Applications

- Lithium-ion battery charging and discharging switch

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Source to Source Voltage	V _{SSS}		20	V
Gate to Source Voltage	V _{GSS}		±10	V
Source Current (DC)	I _S		10	A
Source Current (Pulse)	I _{SP}	PW≤10μs, duty cycle≤1%	60	A
Total Dissipation	P _T	When mounted on ceramic substrate (5000mm ² ×0.8mm)	1.6	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		- 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (5000mm ² ×0.8mm)	R _{θJA}	78.1	°C /W

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Source to Source Breakdown Voltage	V(BR) _{SSS}	I _S =1mA, V _{GS} =0V Test Circuit 1	20			V
Zero-Gate Voltage Source Current	I _{SSS}	V _{SS} =20V, V _{GS} =0V Test Circuit 1			1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{SS} =0V Test Circuit 2			±1.0	μA
Gate Threshold Voltage	V _{GS(th)}	V _{SS} 10V, I _S =1mA Test Circuit 3	0.5		1.3	V
Forward Transconductance	g _{FS}	V _{SS} =10V, I _S =3A Test Circuit 4		11.4		S
Static Source to Source On-State Resistance	R _{SS(on)1}	I _S =3A, V _{GS} =4.5V Test Circuit 5	8.8	11.1	13.3	mΩ
	R _{SS(on)2}	I _S =3A, V _{GS} =4.0V Test Circuit 5	9.1	11.4	13.7	mΩ
	R _{SS(on)3}	I _S =3A, V _{GS} =3.8V Test Circuit 5	9.3	11.6	13.9	mΩ
	R _{SS(on)4}	I _S =3A, V _{GS} =3.1V Test Circuit 5	10.0	12.5	15.6	mΩ
	R _{SS(on)5}	I _S =3A, V _{GS} =2.5V Test Circuit 5	11.1	13.9	17.4	mΩ

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

EFC6605R

Continued from preceding page.

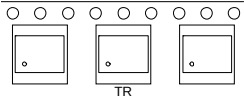
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	$V_{SS}=10V, V_{GS}=4.5V, I_S=3A$ Test Circuit 6		154		ns
Rise Time	t_r			678		ns
Turn-OFF Delay Time	$t_{d(off)}$			44400		ns
Fall Time	t_f			60800		ns
Total Gate Charge	Q_g	$V_{SS}=10V, V_{GS}=4.5V, I_S=10A$ Test Circuit 7		19.8		nC
Forward Source to Source Voltage	$V_{F(S-S)}$	$I_S=3A, V_{GS}=0V$ Test Circuit 8		0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

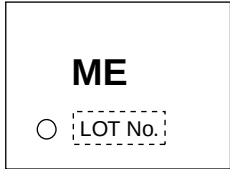
Ordering & Package Information

Device	Package	Shipping	note
EFC6605R-TR	EFCP	5,000 pcs. / reel	Pb-Free and Halogen Free

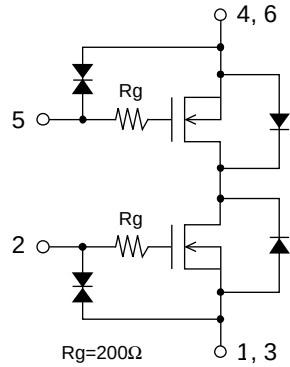
Packing Type: TR



Marking

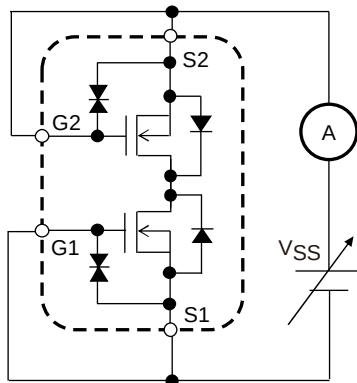


Electrical Connection

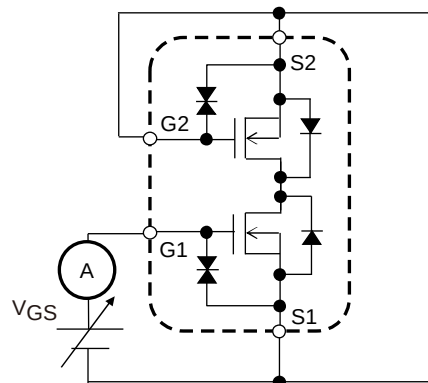


Test circuits are example of measuring FET1 side

Test Circuit 1
 I_{SSS}

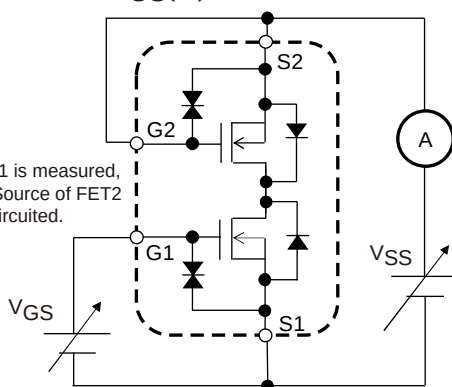


Test Circuit 2
 I_{GSS}



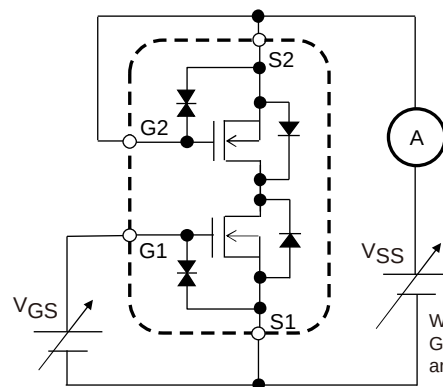
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3
 $V_{GS(th)}$



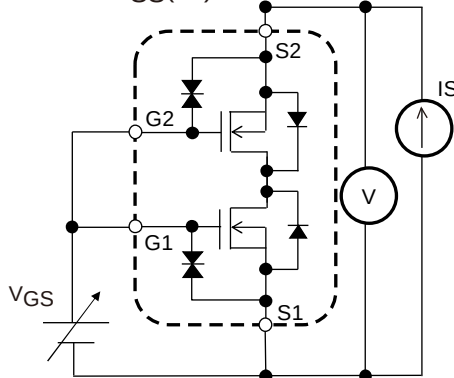
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4
 g_{FS}

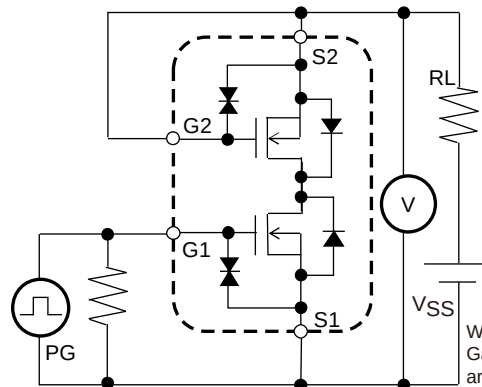


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 5
 $R_{SS(on)}$

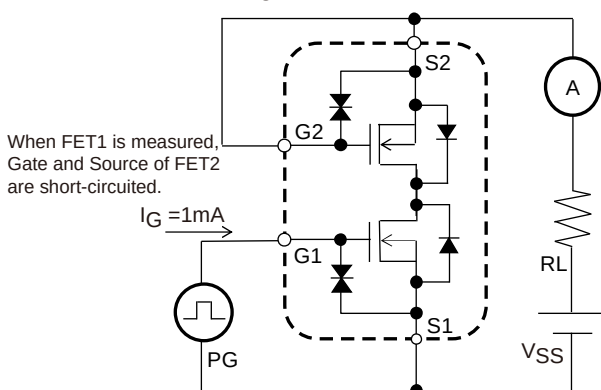


Test Circuit 6
 $t_{d(on)}$, t_r , $t_{d(off)}$, t_f



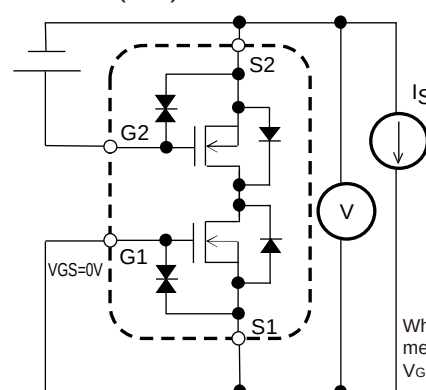
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 7
 Q_g



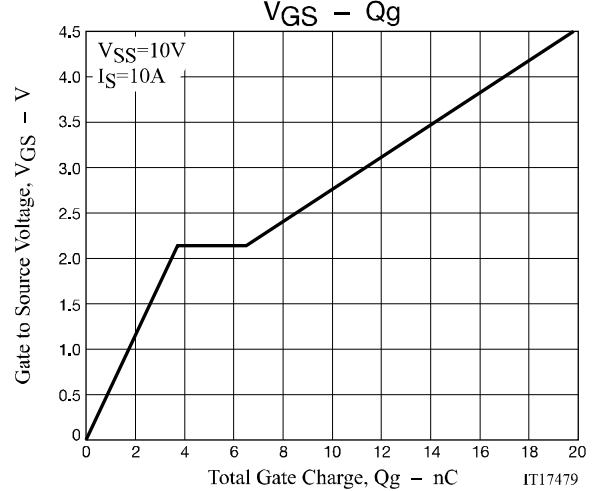
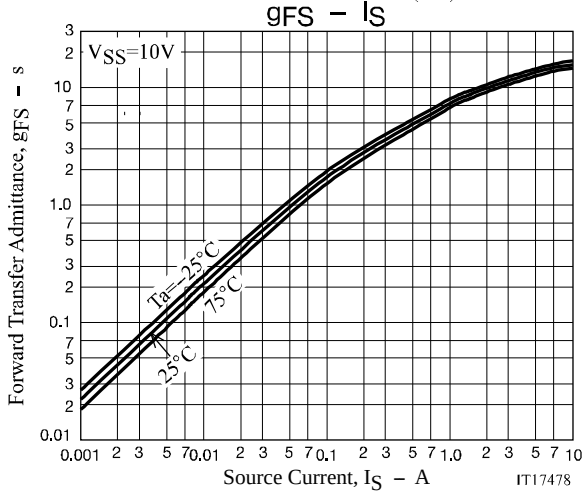
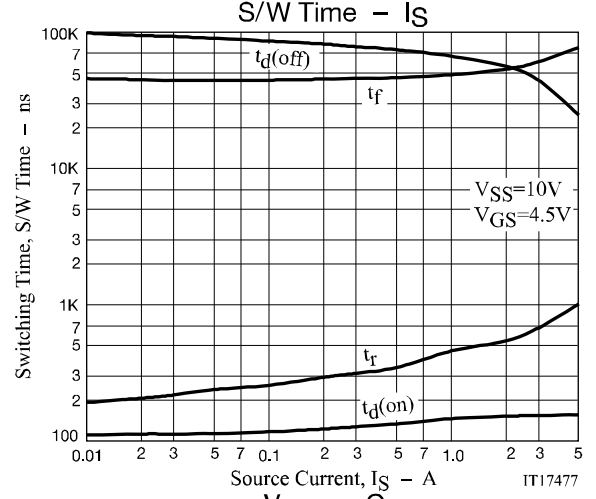
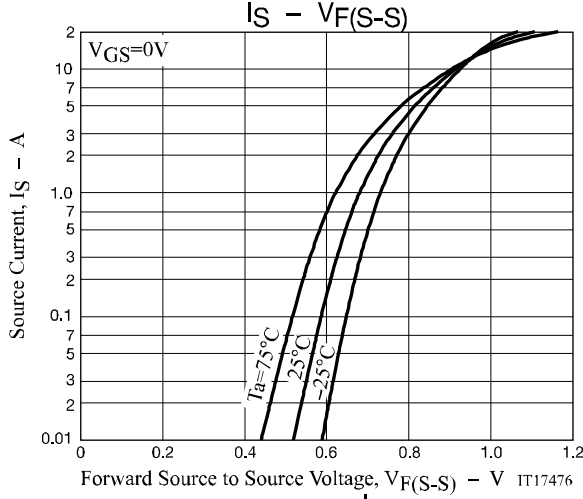
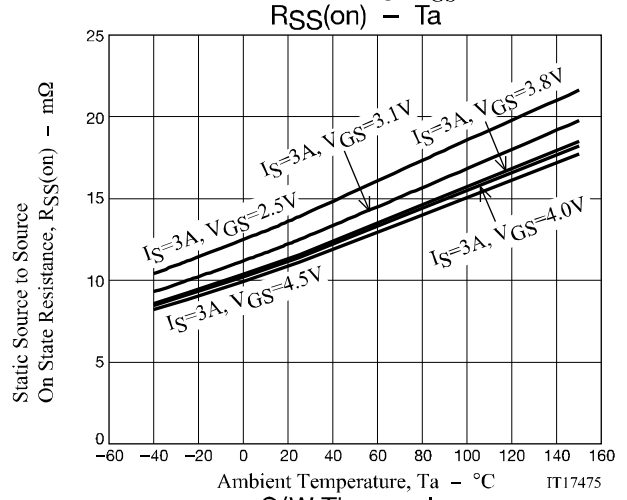
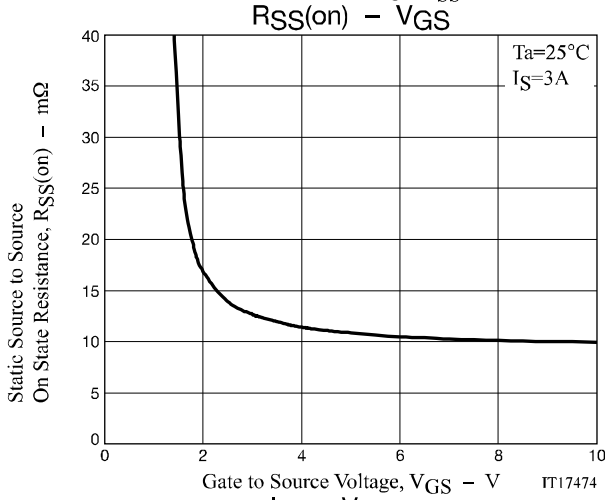
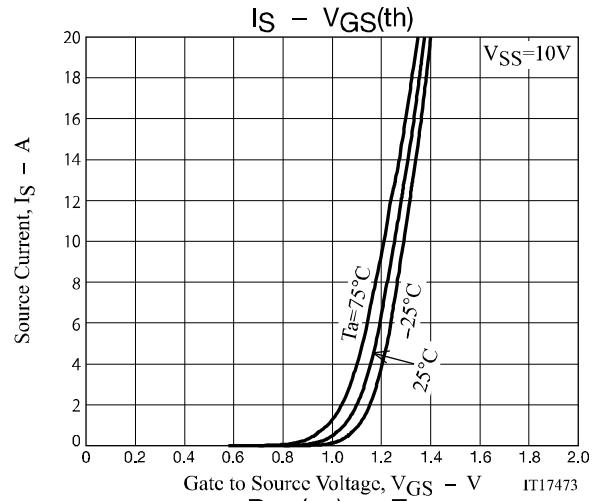
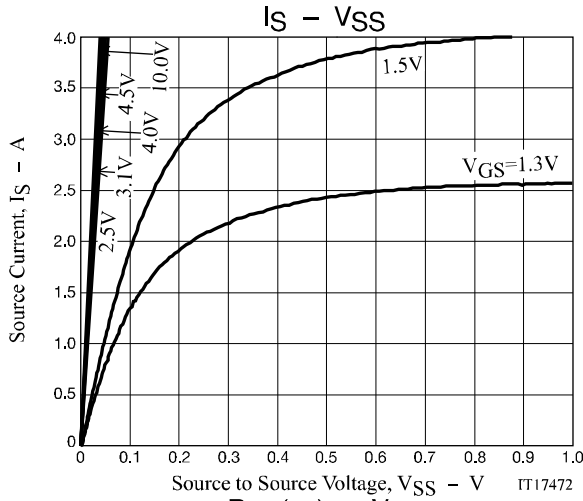
When FET1 is measured, Gate and Source of FET2 are short-circuited.

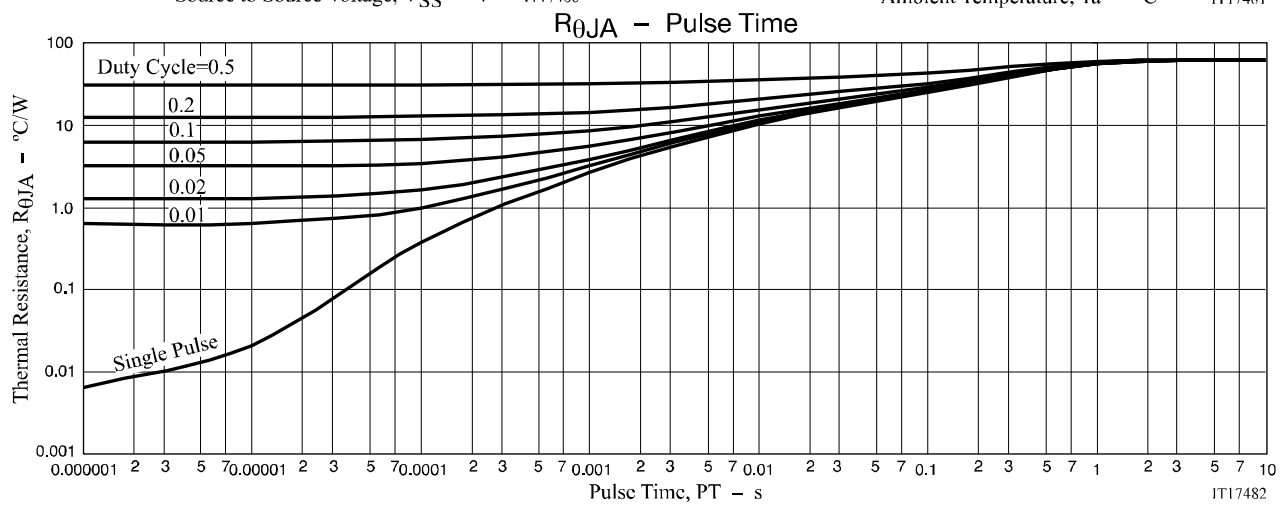
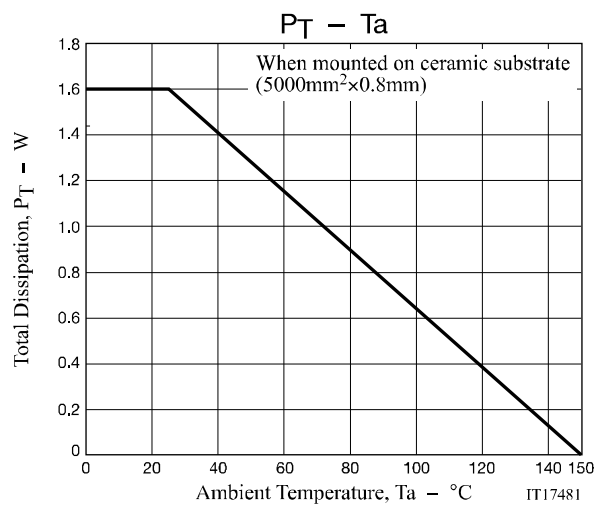
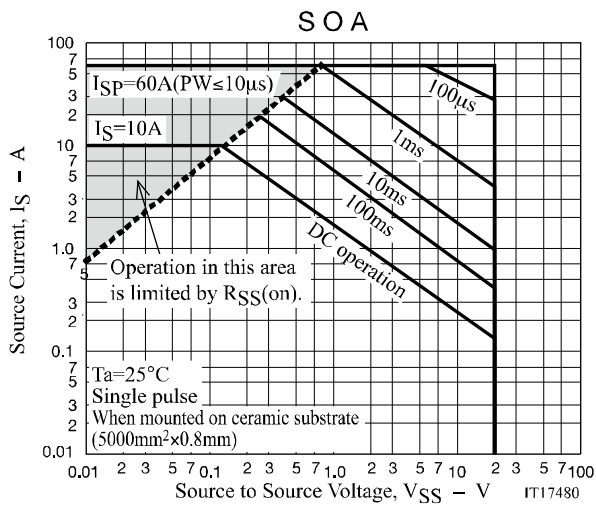
Test Circuit 8
 $V_F(S-S)$



When FET1 is measured, +4.5V is added to V_{GS} of FET2.

When FET2 is measured, the position of FET1 and FET2 is switched.





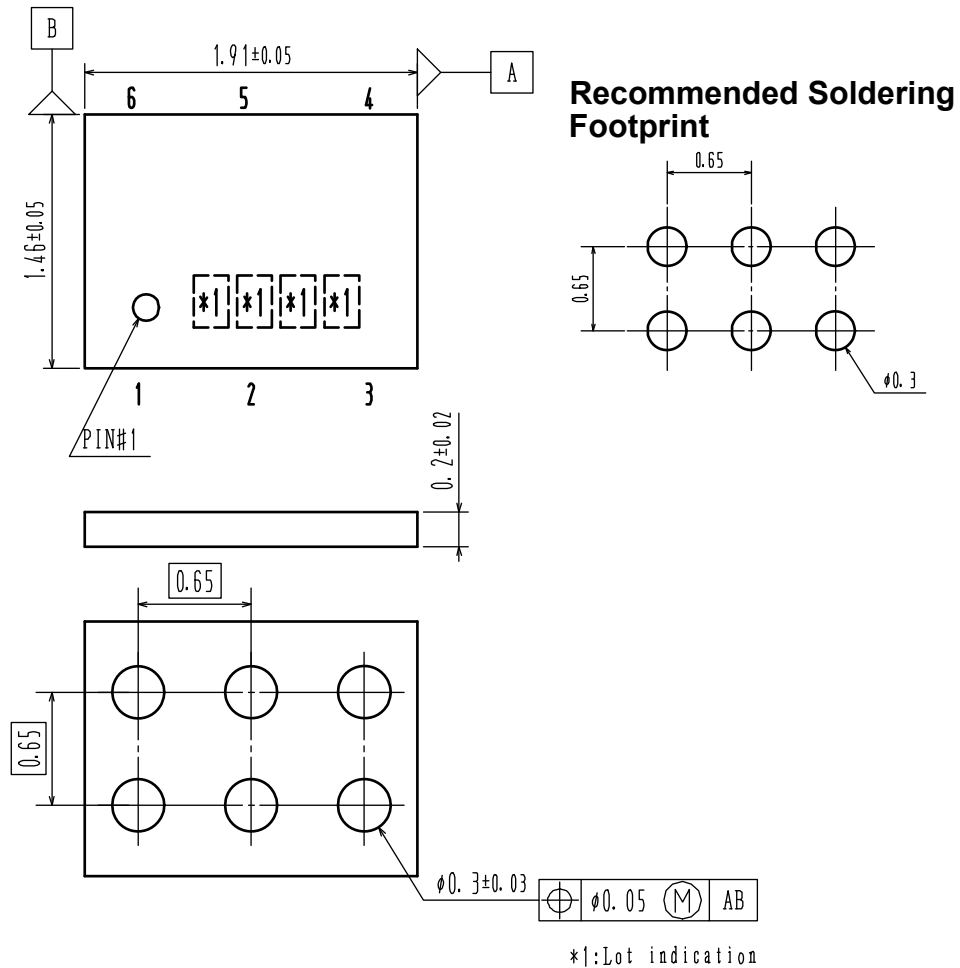
Package Dimensions

EFC6605R-TR

EFCP1915-6CE-020

unit : mm

- 1: Source1
- 2: Gate1
- 3: Source1
- 4: Source2
- 5: Gate2
- 6: Source2



Note on usage : Since the EFC6605R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9